NPN Silicon Planar Power Transistor 100VcBo, 15A lc, TO-3





RoHS Compliant

General Purpose Switching and Amplifier Applications

Absolute Maximum Ratings

Description	Symbol	Value	Units	
Collector Base Voltage	Vсво	100		
Collector Emitter Voltage	Vceo	60]	
Collector Emitter Voltage(RBE=100W)	Vcer	70	V	
Emitter Base Voltage	VEBO	7]	
Collector Current Continuous	lc	15	^	
Base Current	lв	7	- A	
Power Dissipation @ Tc=25°C Derate Above 25°C	Ртот	115 0.657	W W/°C	
Operating and Storage Junction Temperature Range	Тл, Тэтв	- 65 to +200	°C	

Thermal Resistance

Junction to Case R _{th(j-c)}	1.52	°C/W
---------------------------------------	------	------

Electrical Characteristics (TC=25°C unless specified otherwise)

Description	Symbol	Test Condition	Min	Max	Units
Collector Emitter Sustaining Voltage	VcEO(sus)*	Ic=200mA, I _B =0	60		
Collector Emitter Sustaining Voltage	VCER(sus)*	Ic=200mA, R _{BE} =100Ω	70		
	Icex	Vce=100V, VBE=(off)=1.5V		1	mA
Collector Cut off Current		Tc=150°C Vc==100V, Vb==(off)=1.5V		5	
Collector Cut off Current	Iceo	Vce=30V, I _B =0		0.7	mA
Emitter Cut off Current	leво	V _{BE} =7V, I _C =0		5	mA
Collector Emitter Saturation Voltage	Vce(Sat) *	Ic=4A, IB=400mA Ic=10A, IB=3.3A		1.1 3	V
Base Emitter on Voltage	VBE(on) *	Ic=4A, VcE=4V		1.5	V
DC Current Gain	hfe*	Ic=4A, Vc==4V Ic=10A, Vc==4V	20 5	80	

^{*}Pulse Test: Pulse Width <300ms, Duty Cycle <2%

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro



NPN Silicon Planar Power Transistor

100Vсво, 15A Ic, ТО-3



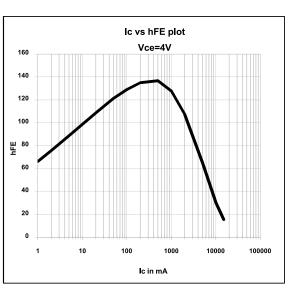
Second Breakdown

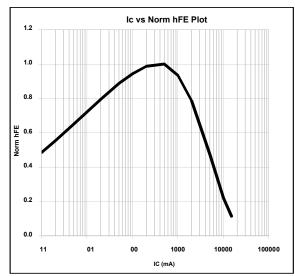
Description	Symbol	Test Condition	Min	Max	Units
Second Breakdown Collector Current with Base Forward Biased	ls/b	VcE=40V, t=1 s, Nonrepetitive	2.87		А

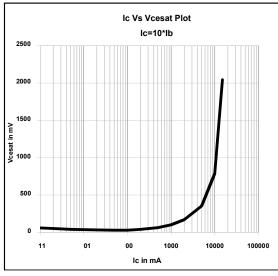
Dynamic Characteristics

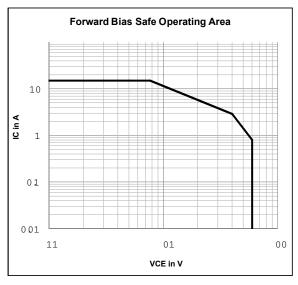
Current Gain - Bandwidth Product	fτ	Ic=0.5A, Vc==10V, f=1MHz	2.5		MHz
Small Signal Current Gain	hfe	Ic=1A, Vc==4V, f=1kHz	15	120	
Small Signal Current Gain Cutoff Frequency	fHFE	Ic=1A, VcE=4V, f=1kHz	10		kHz

Characteristics Plots









Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro

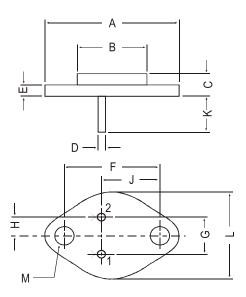


NPN Silicon Planar Power Transistor

100Vсво, 15A Ic, ТО-3



TO-3 Metal Can Package



Dim	Min.	Max.
А	_	39.37
В		22.22
С	6.35	8.5
D	0.96	1.09
Е		1.77
F	29.9	30.4
G	10.69	11.18
Н	5.2	5.72
J	16.64	17.15
K	11.15	12.25
L	_	26.67
М	3.84	4.19

Dimensions: Millimetres



Pin Configuration

- 1. Base
- 2. Emitter
- 3. Collector

Part Number Table

Description	Part Number	
NPN Silicon Planar Power Transistor, 100 VcBo, 15A lc, TO-3	2N3055	

Important Notice: This data sheet and its contents (the "Information") belong to the members of the AVNET group of companies (the "Group") or are licensed to it. No licence is granted for the use of it other than for information purposes in connection with the products to which it relates. No licence of any intellectual property rights is granted. The Information is subject to change without notice and replaces all data sheets previously supplied. The Information supplied is believed to be accurate but the Group assumes no responsibility for its accuracy or completeness, any error in or omission from it or for any use made of it. Users of this data sheet should check for themselves the Information and the suitability of the products for their purpose and not make any assumptions based on information included or omitted. Liability for loss or damage resulting from any reliance on the Information or use of it (including liability resulting from negligence or where the Group was aware of the possibility of such loss or damage arising) is excluded. This will not operate to limit or restrict the Group's liability for death or personal injury resulting from its negligence. Multicomp Pro is the registered trademark of Premier Farnell Limited 2019.

Newark.com/multicomp-pro Farnell.com/multicomp-pro Element14.com/multicomp-pro

